

Fig. 1A

develop
and rinse

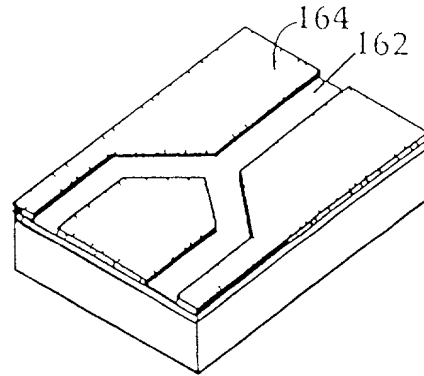


Fig. 1B

1. etch SiO_2
2. remove resist

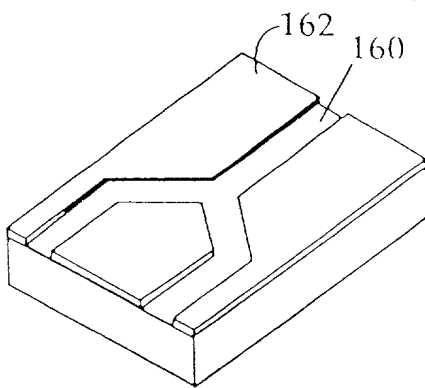


Fig. 1C

etch Si

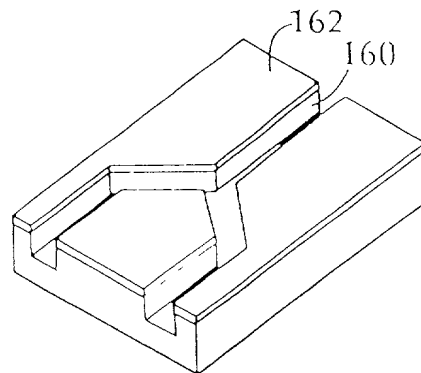


Fig. 1D

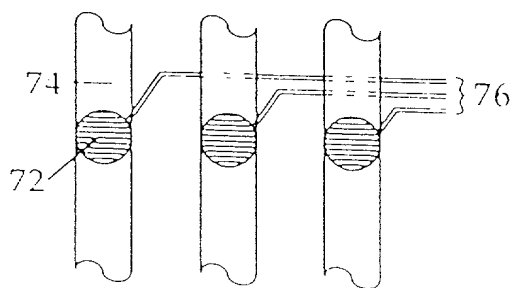


Fig. 2A

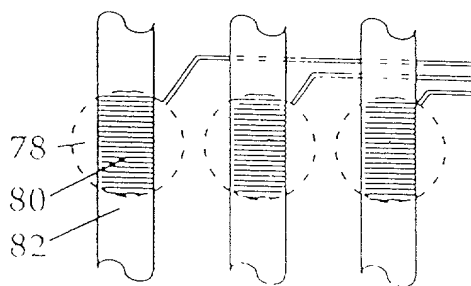


Fig. 2B

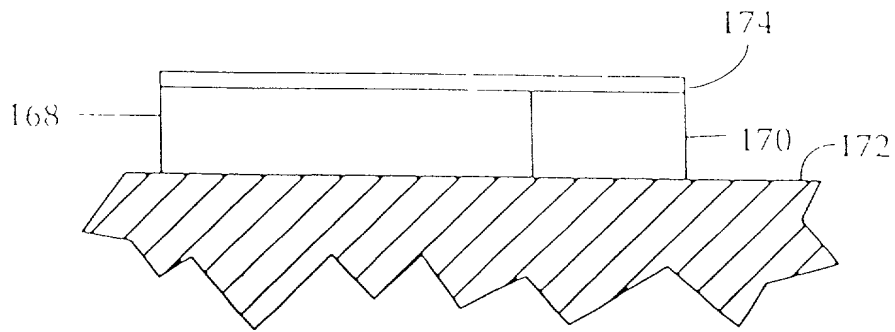


Fig. 3A

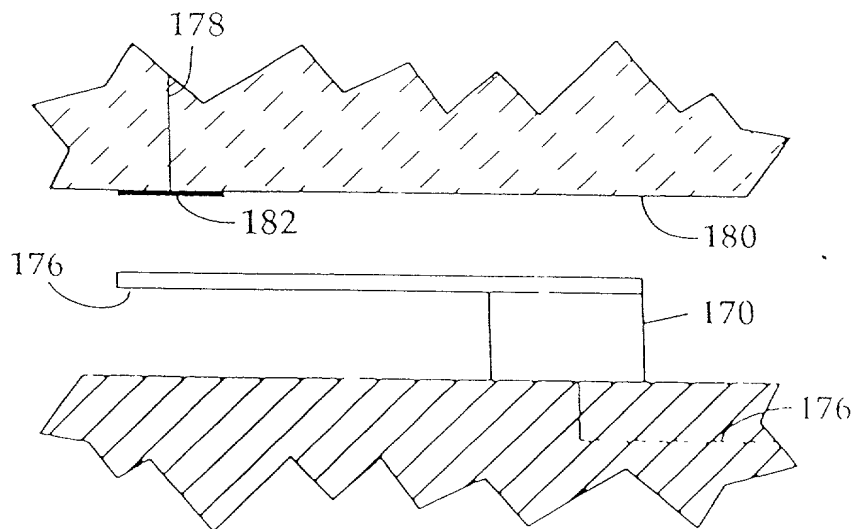


Fig. 3B

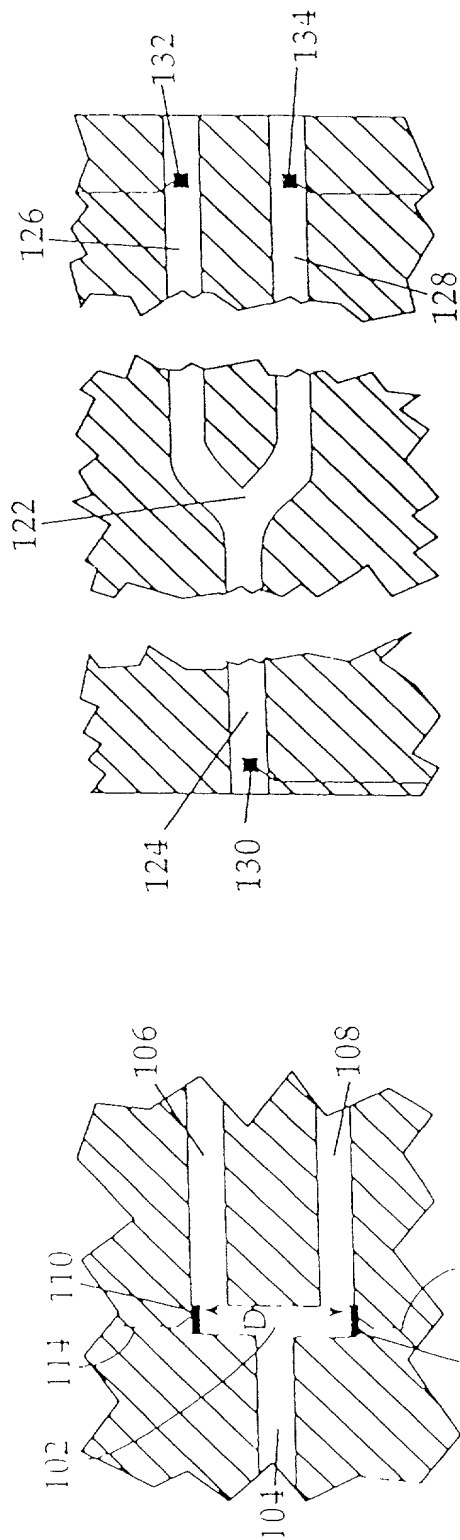


Fig. 4B

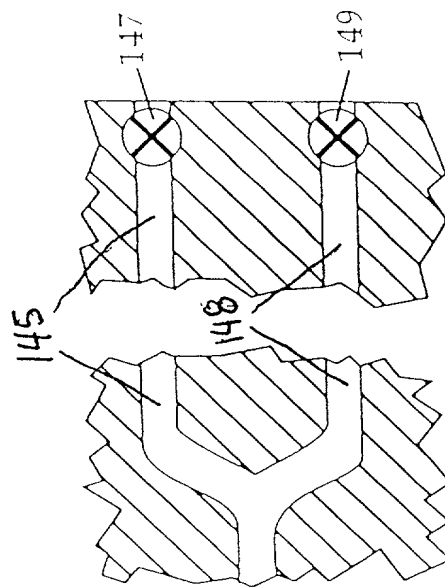


Fig. 4D

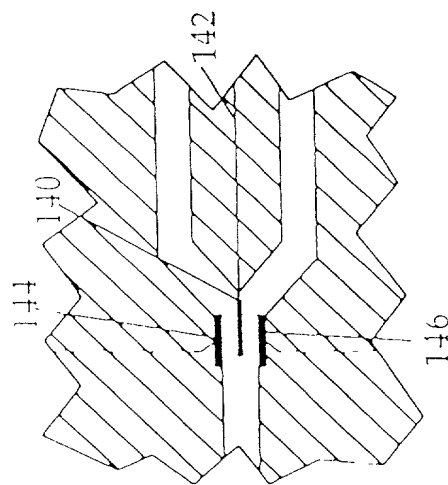


Fig. 4C

TOP SECRET

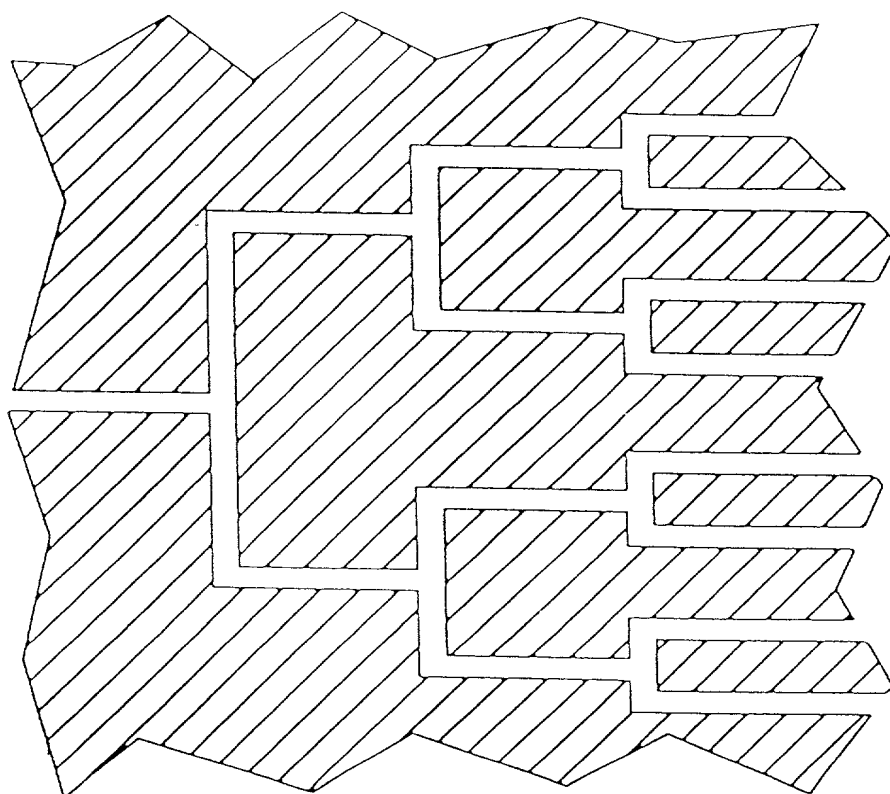


Fig. 5

FOI b7D - 06582660



Fig 6

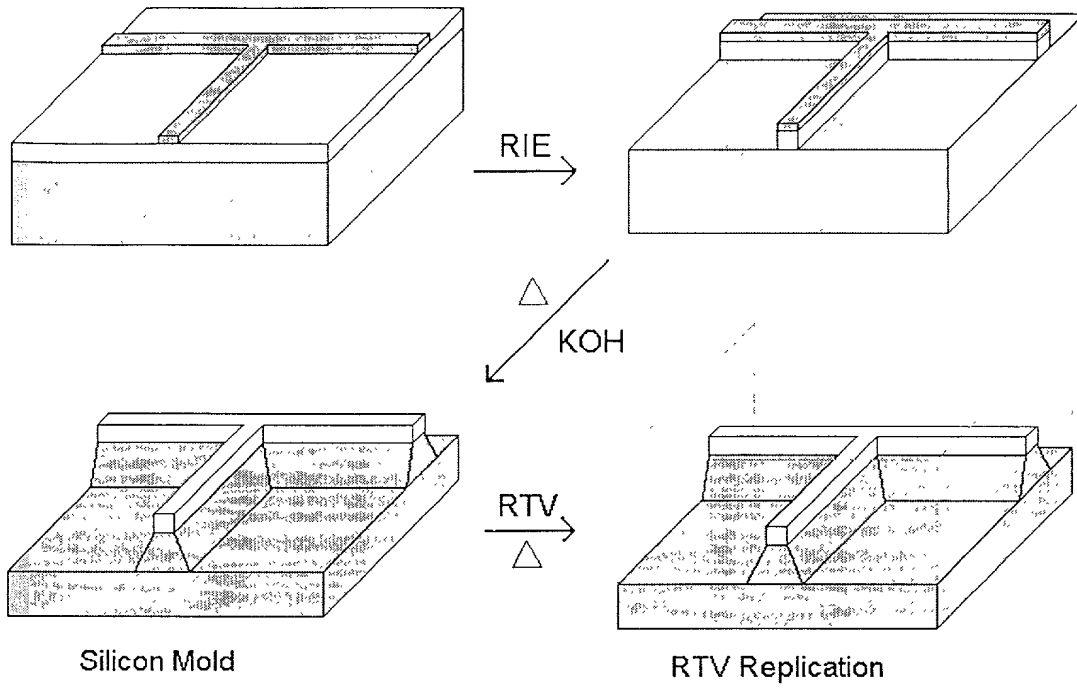


Fig. 7

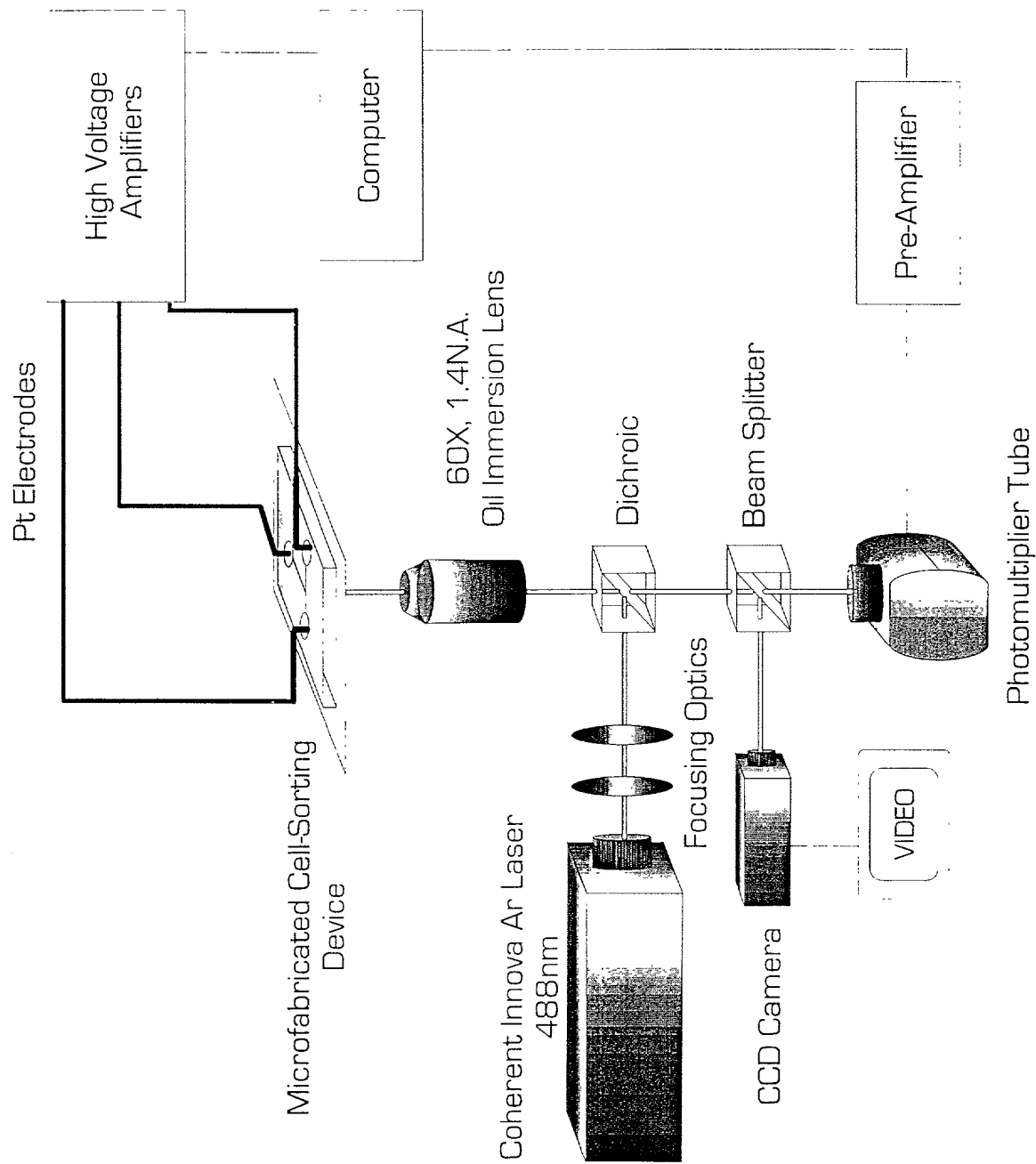


Fig 8

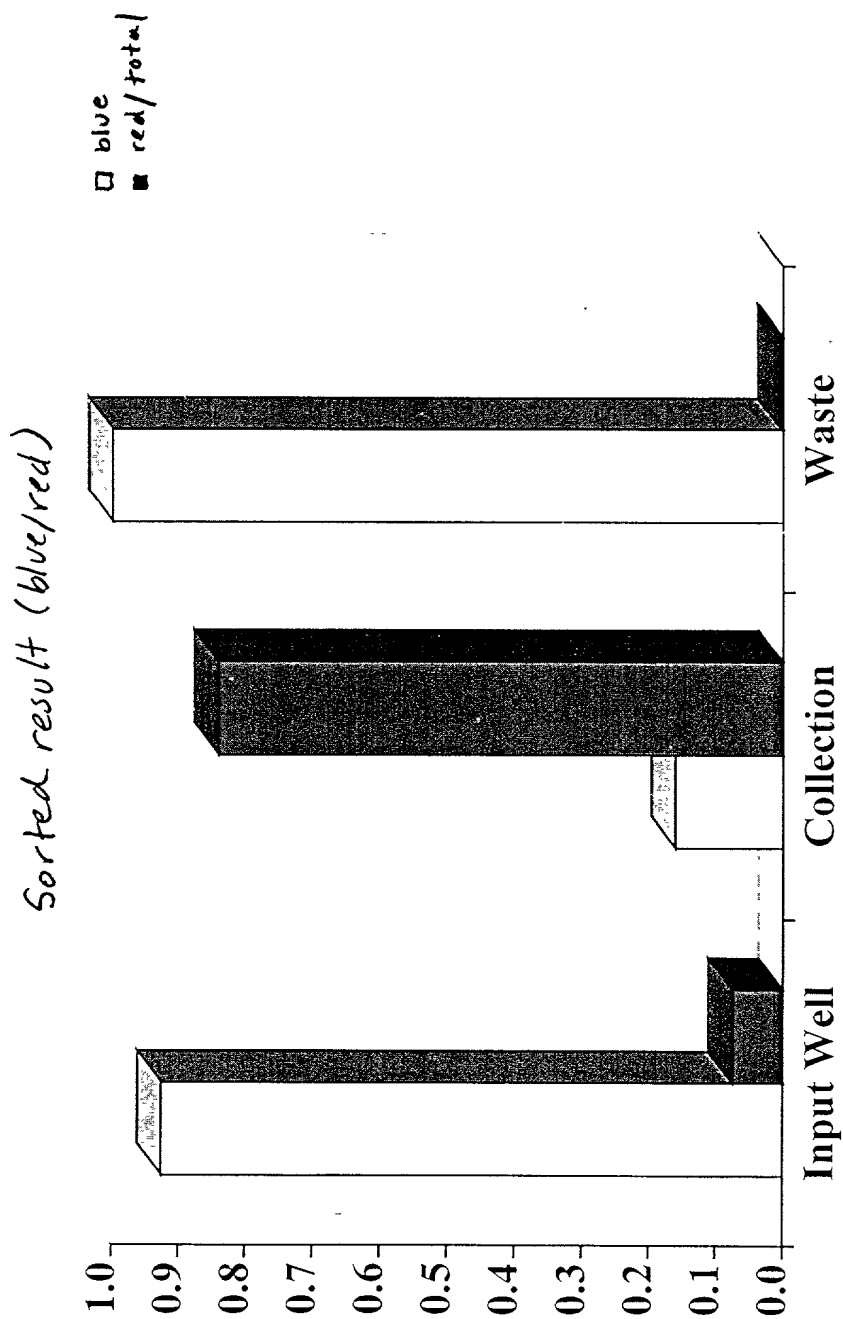


Fig. 9

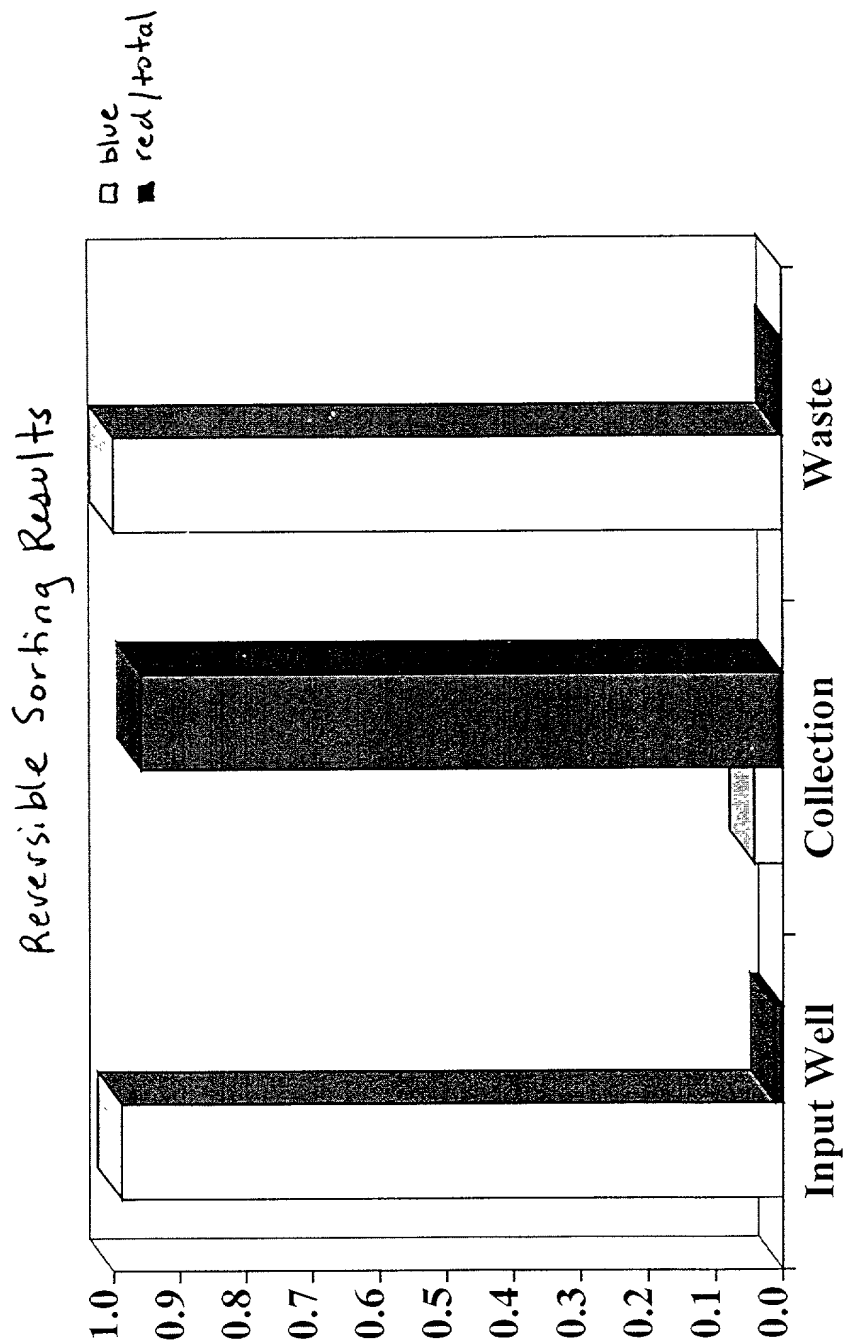


Fig. 10

06522650

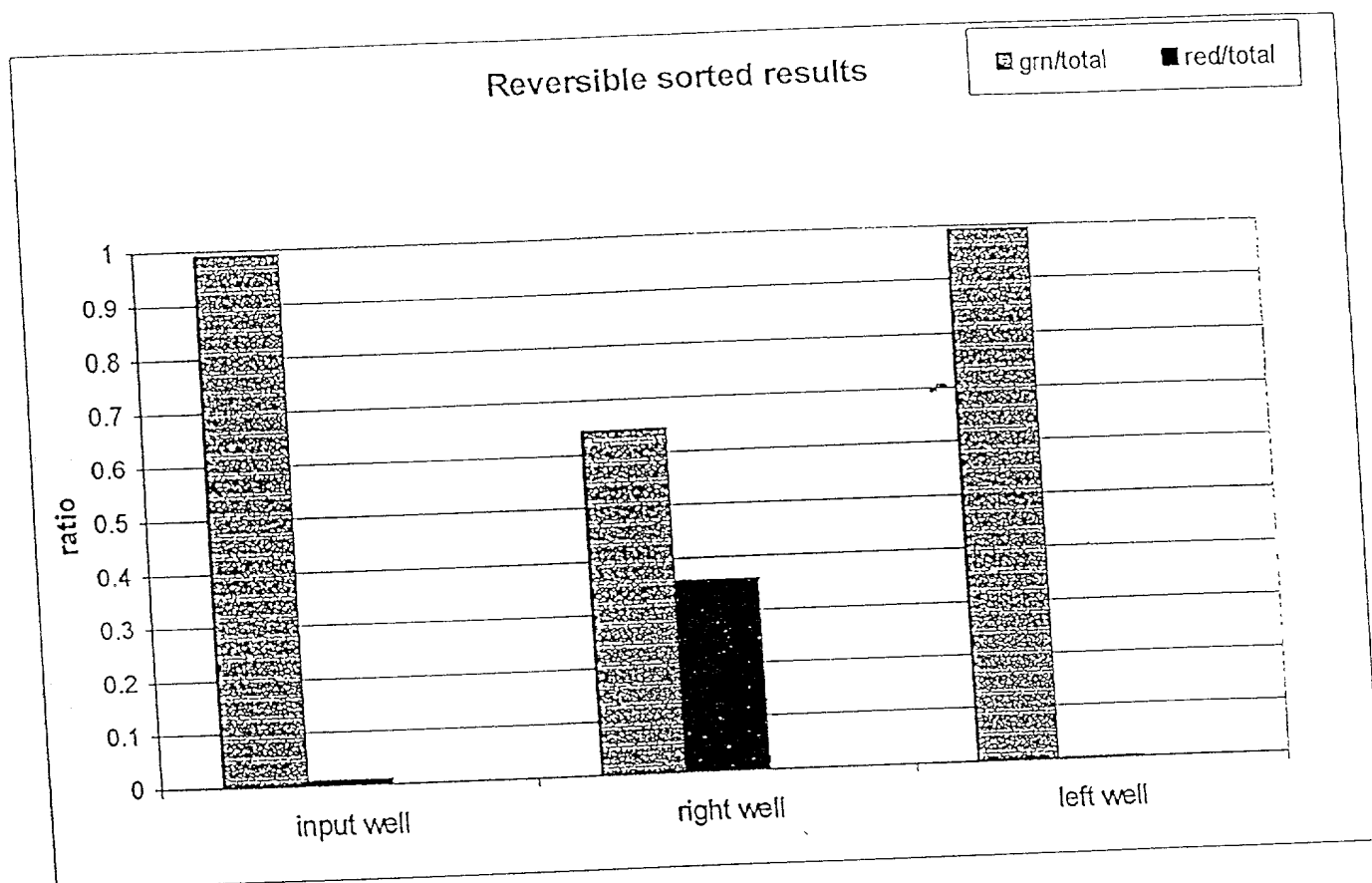


FIGURE 11

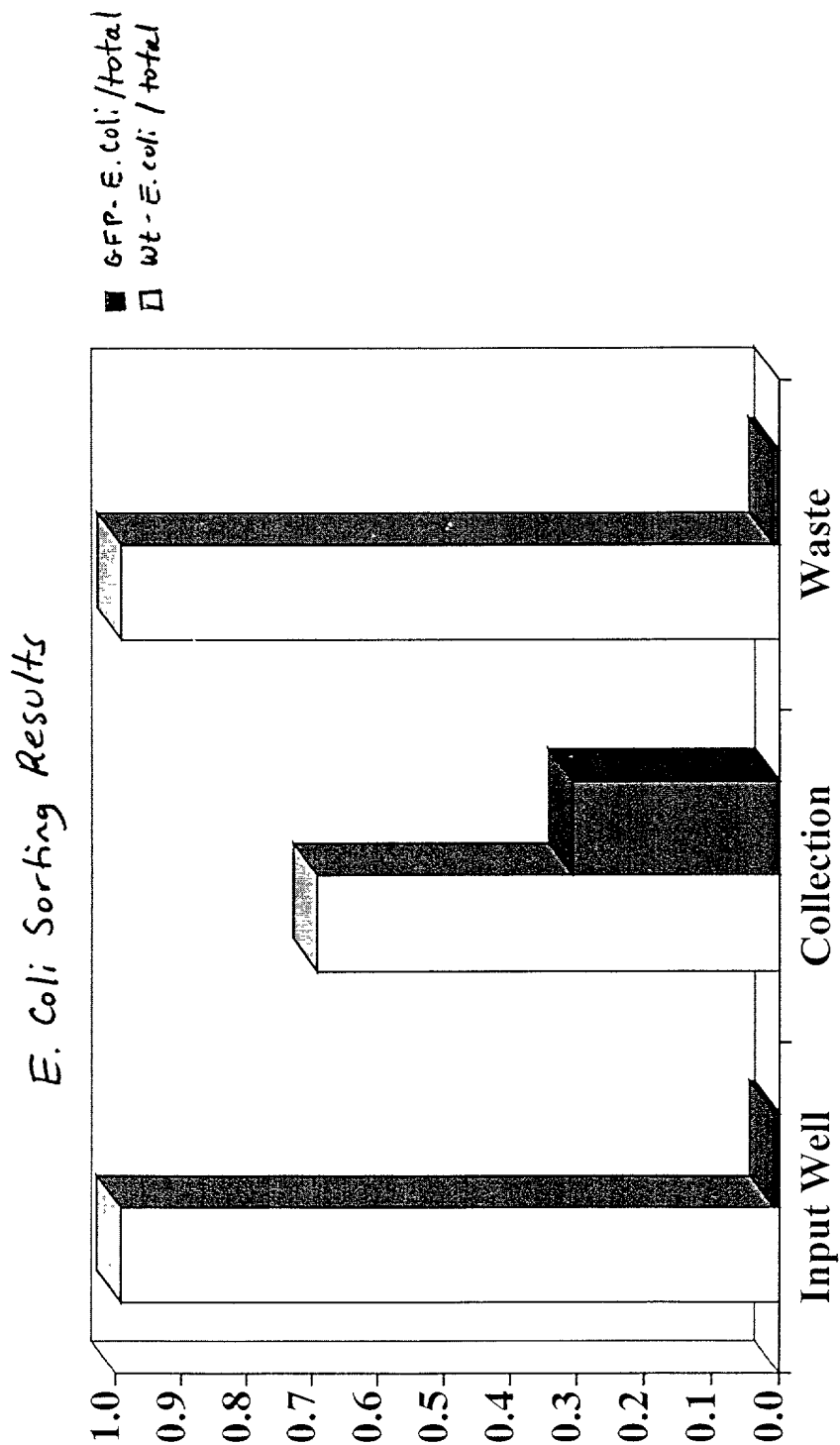


Fig. 12

TOP SECRET 06532660

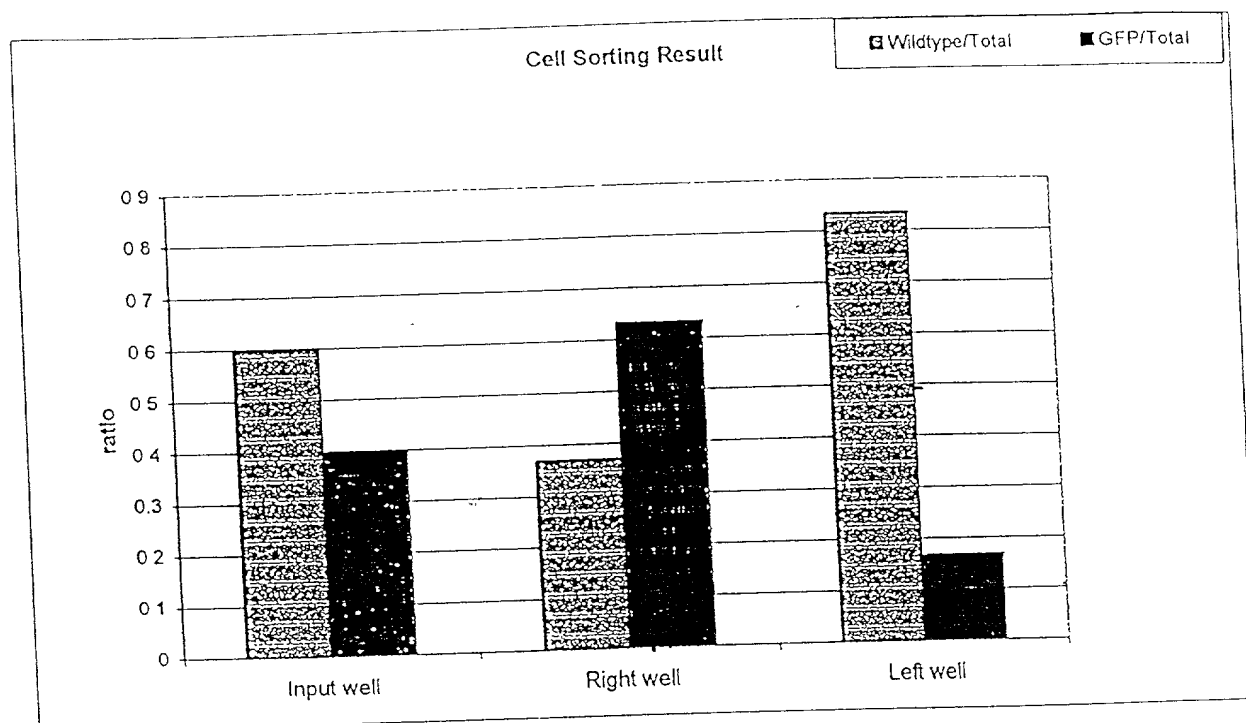
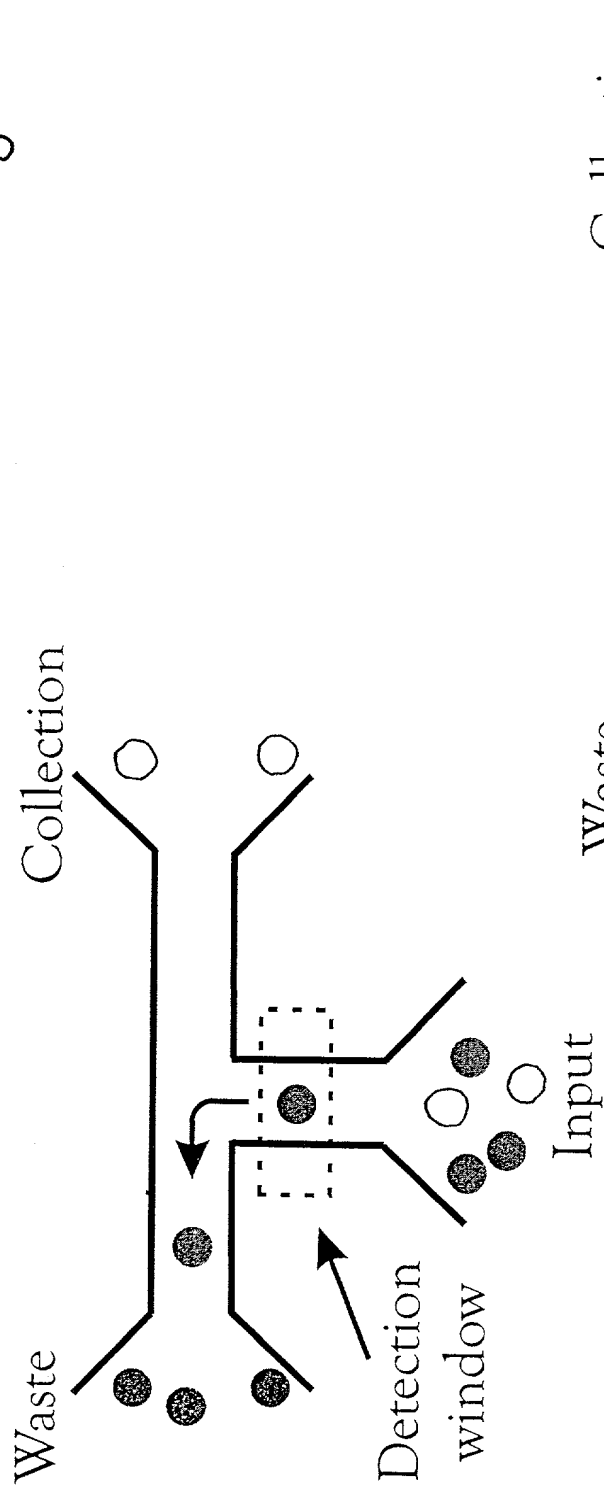
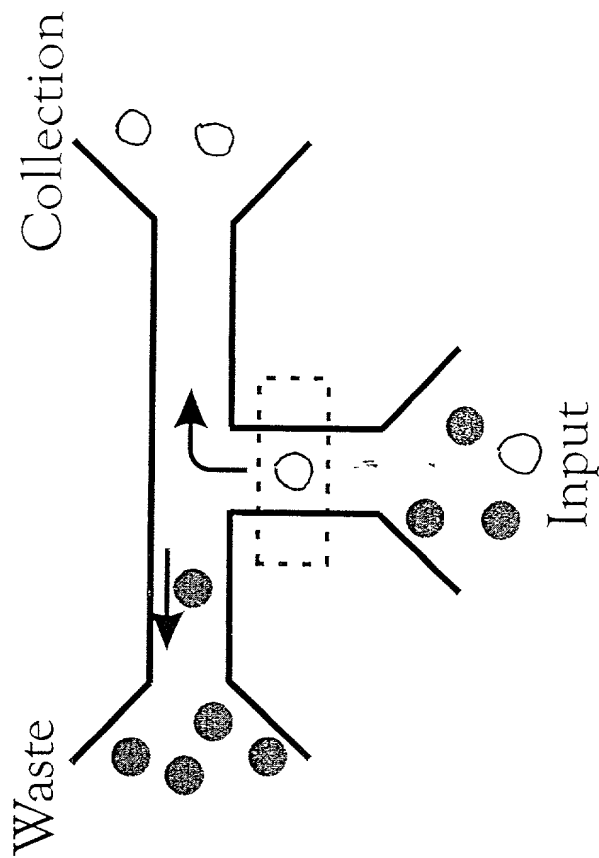


FIGURE 13

Fig. 14

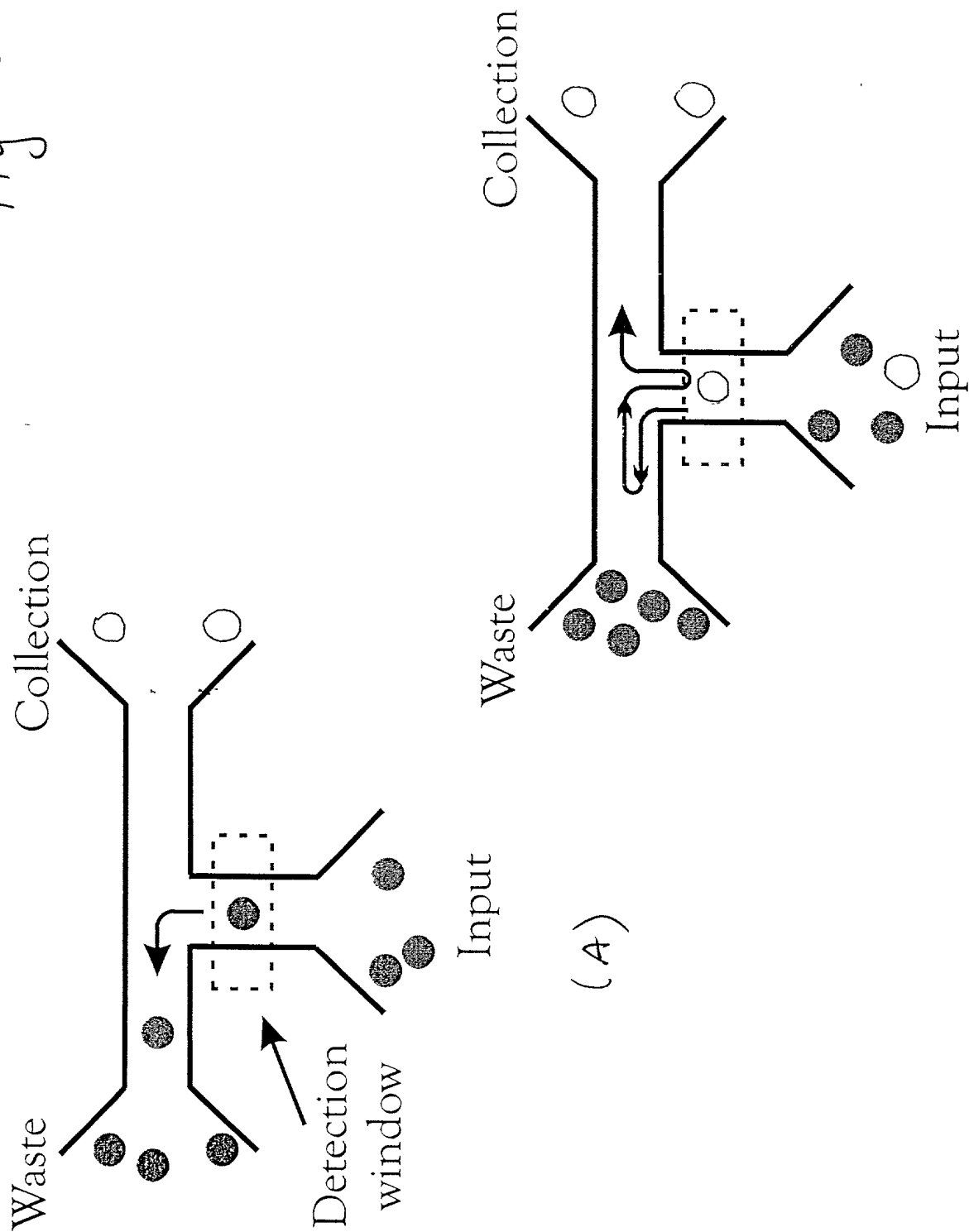


(A)



(B)

Fig 15



(A)

(B)